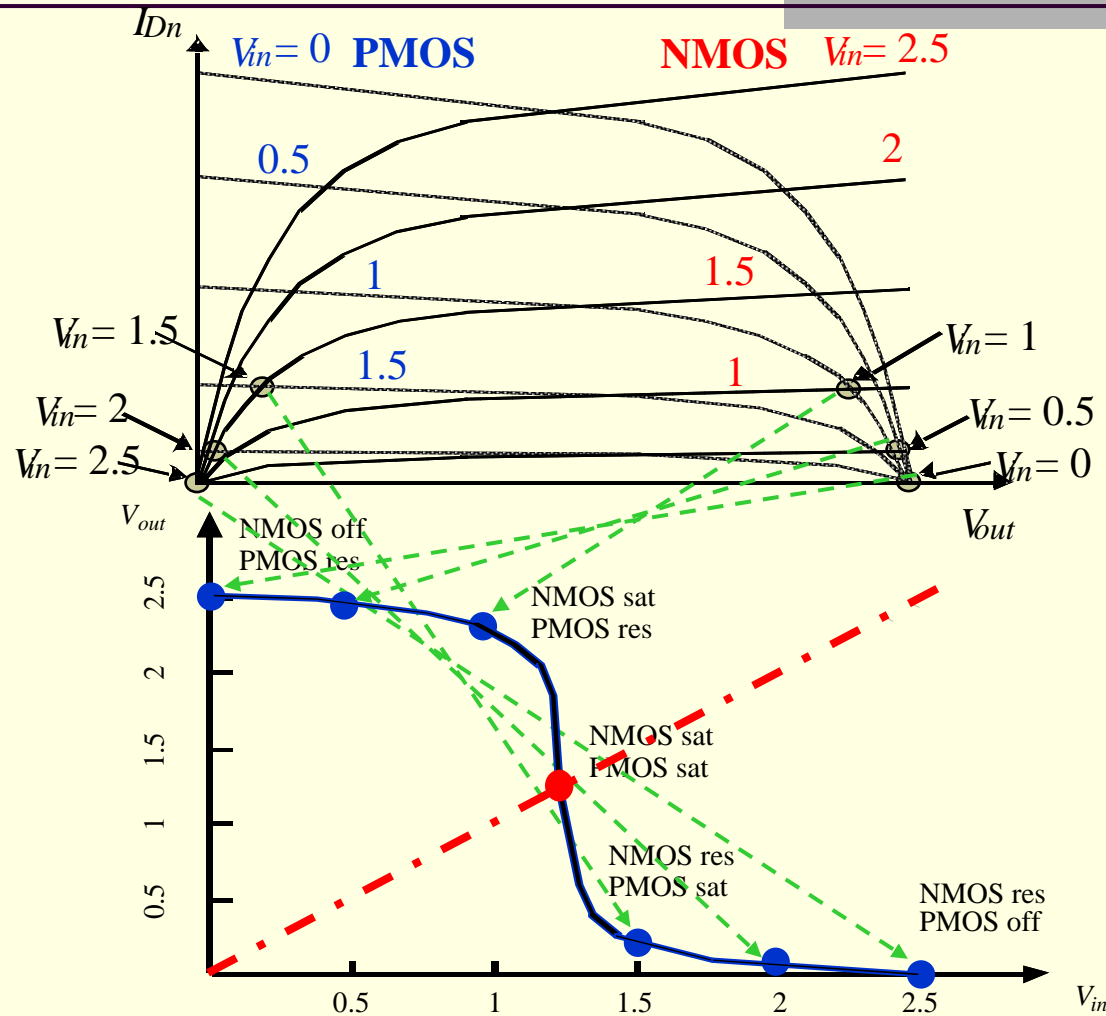
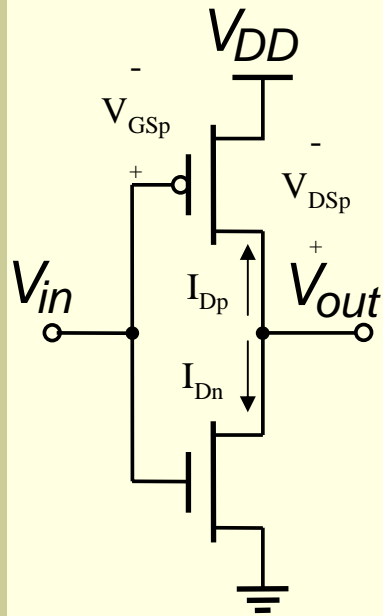


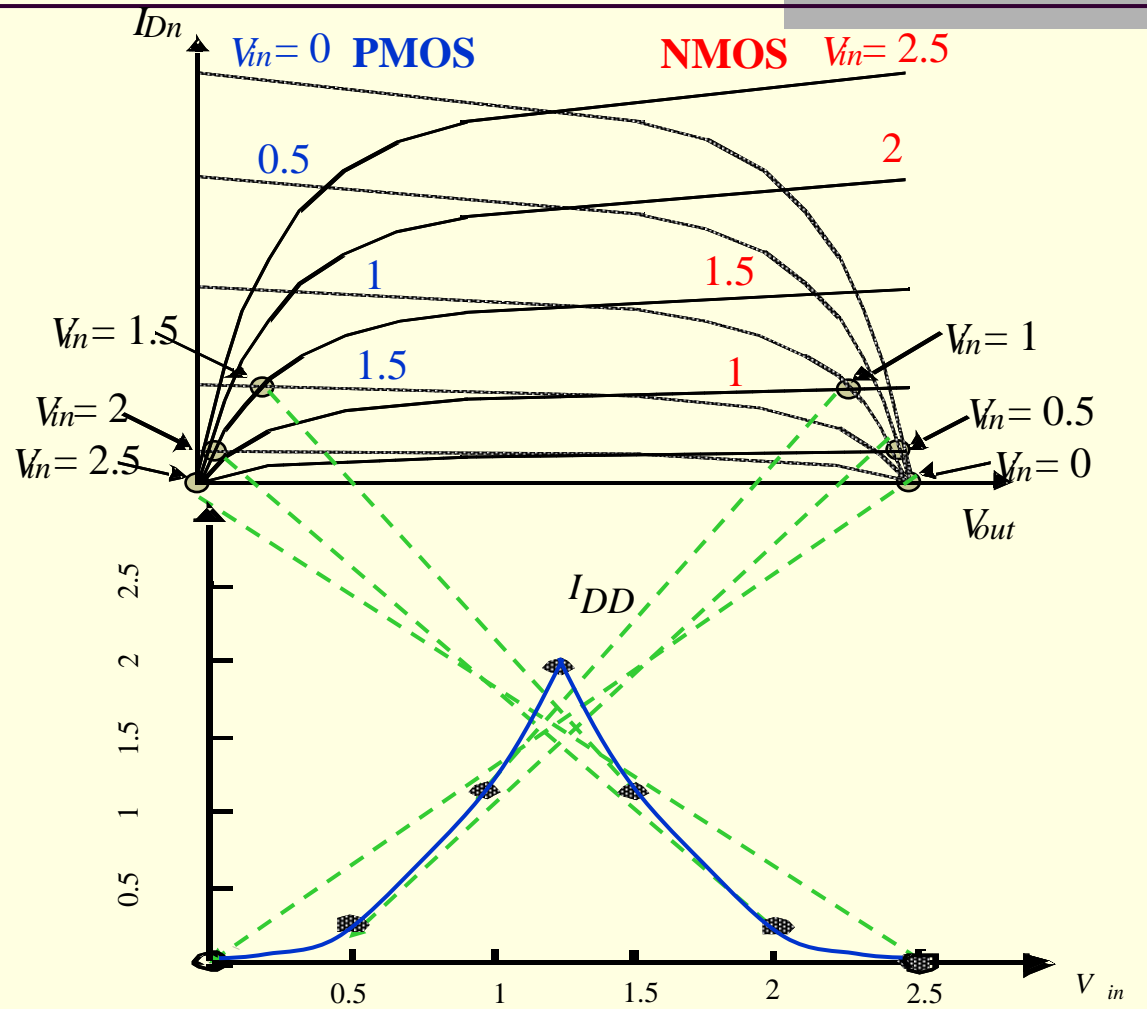
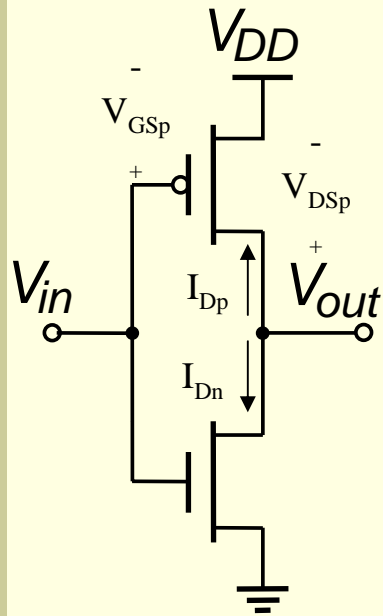
Static characteristics - 4

VTC



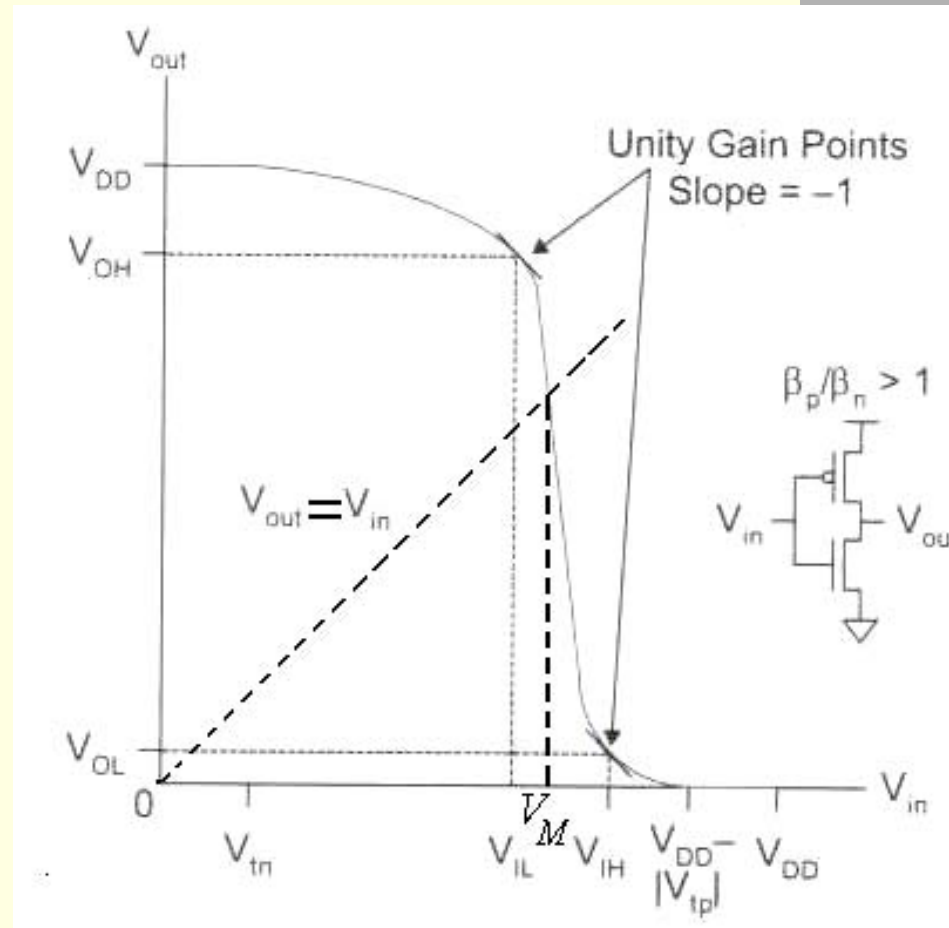
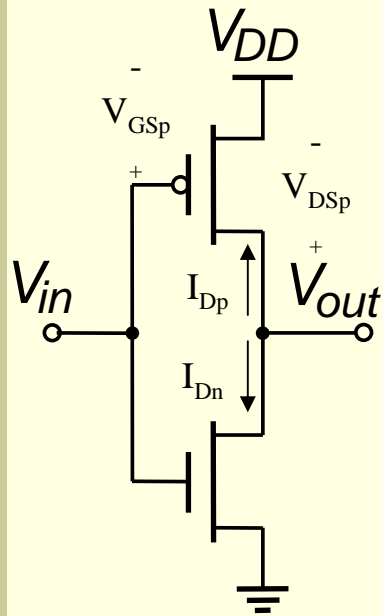
Source: Rabaey

Static characteristics - 5 Short-circuit current

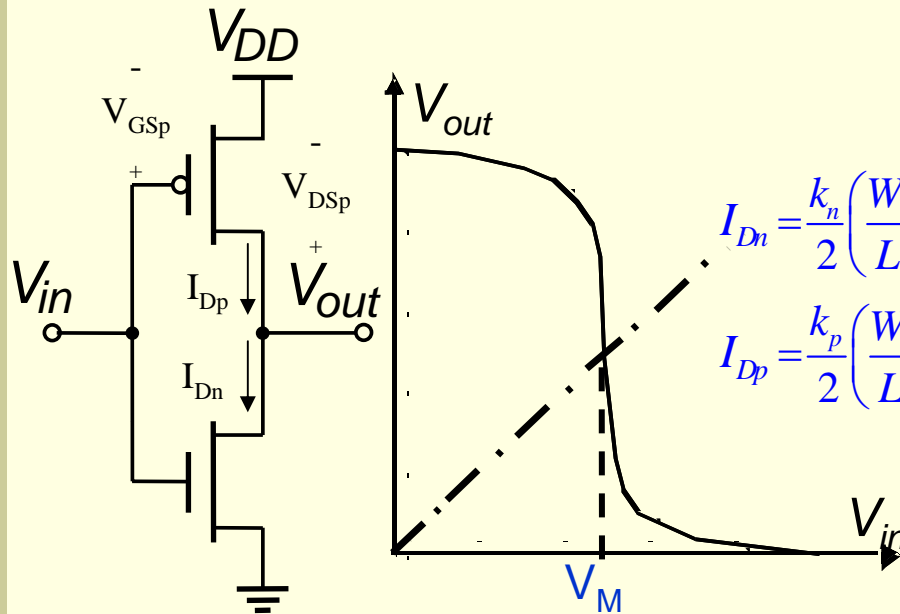


Source: Rabaey

Static characteristics - 6 Switching threshold - 1



Static characteristics - 7 Switching threshold - 2



Experimental determination of V_M :
short-circuit between input and output

$$I_{Dn} = \frac{k_n}{2} \left(\frac{W}{L}\right)_n (V_{GSn} - V_{Tn})^2 (1 + \lambda_n V_{DSn}) \cong \frac{k_n}{2} \left(\frac{W}{L}\right)_n (V_M - V_{Tn})^2$$

$$I_{Dp} = \frac{k_p}{2} \left(\frac{W}{L}\right)_p (V_{GSp} - V_{Tp})^2 (1 + \lambda_p |V_{DSp}|) \cong \frac{k_p}{2} \left(\frac{W}{L}\right)_p (V_{DD} - V_M - |V_{Tp}|)^2$$

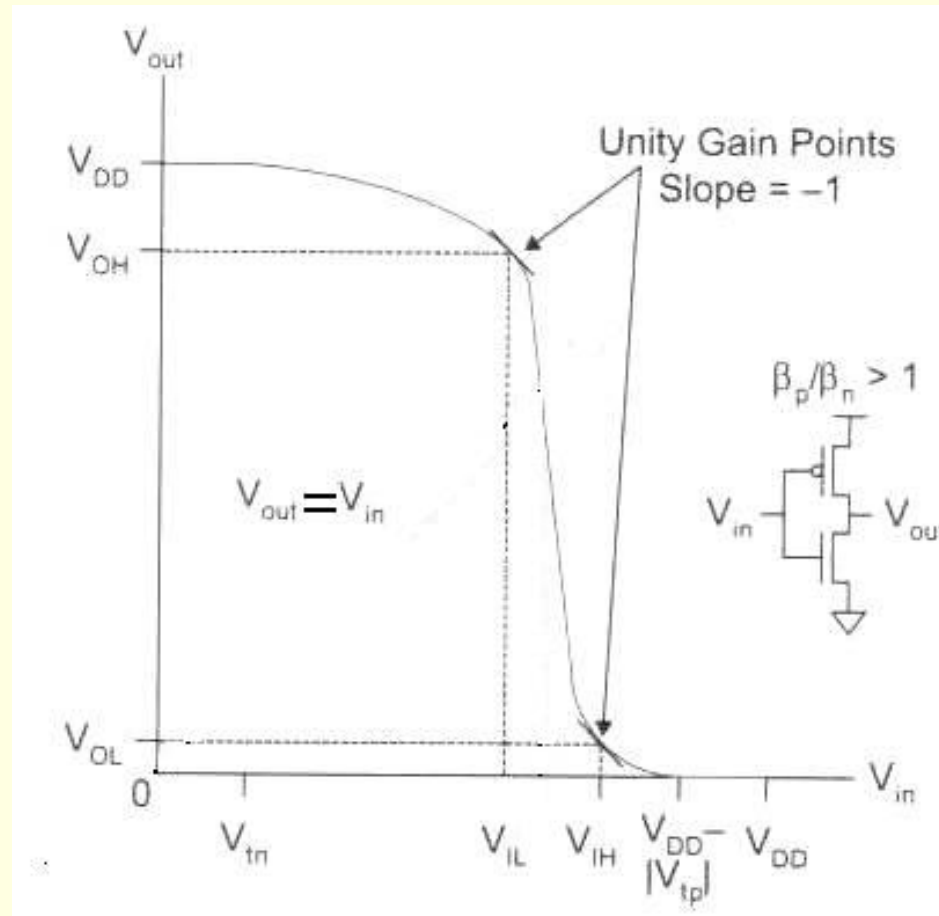
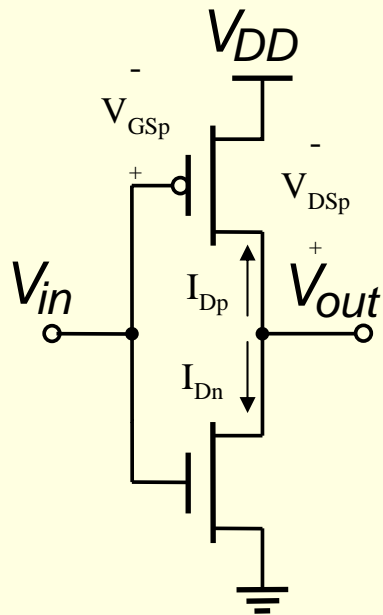
Usually $\lambda V_{DS} \ll 1$

$$I_{Dn} = I_{Dp} \rightarrow V_M = \frac{V_{Tn} + rV_{Tp}}{1+r} + \frac{rV_{DD}}{1+r};$$

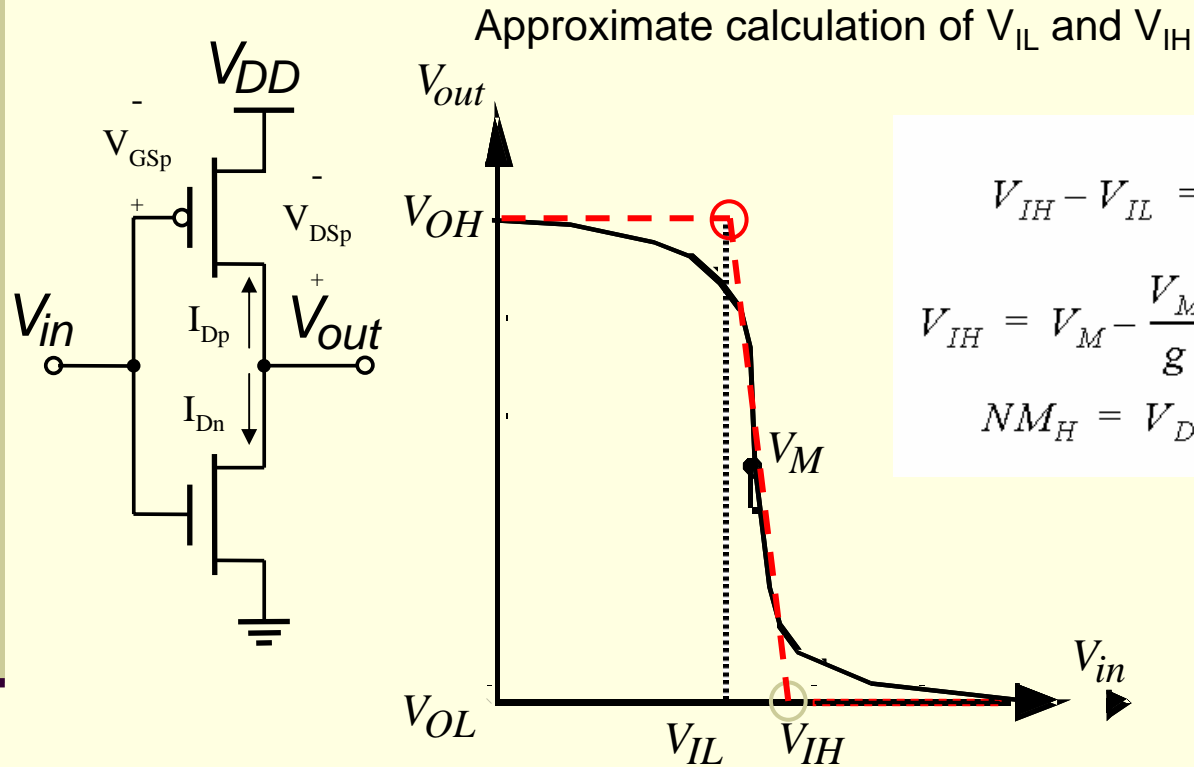
$$r = \sqrt{\frac{k_p}{k_n} \frac{(W/L)_p}{(W/L)_n}}$$

Example: $V_{DD}=2.5$ V, $V_{Tp}=-0.4$ V, $V_{Tn}=0.43$ V. What is V_M for $r=0.5$, 1.0 , and 1.5 ? **Answer:** $V_M=0.98$, 1.26 , and 1.43 V, respectively.

Static characteristics - 8 Noise margins - 1



Static characteristics - 9 Noise margins - 2



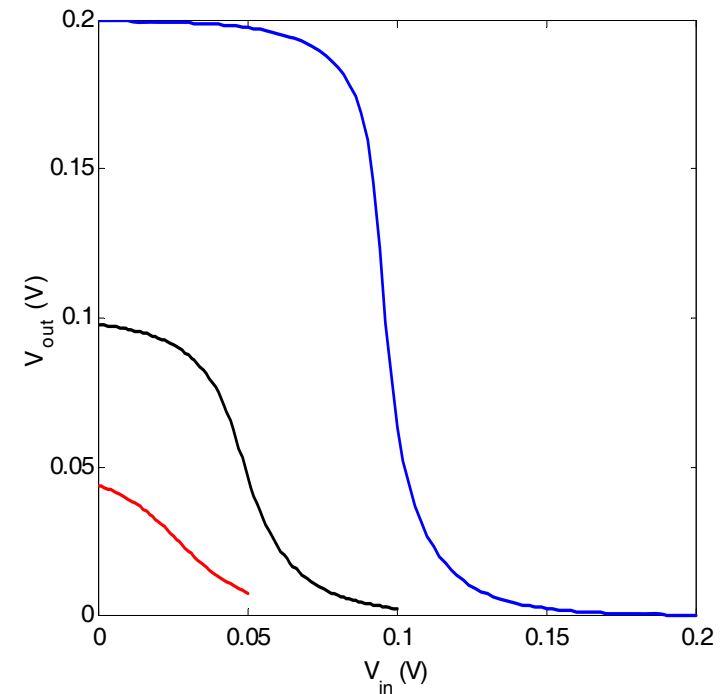
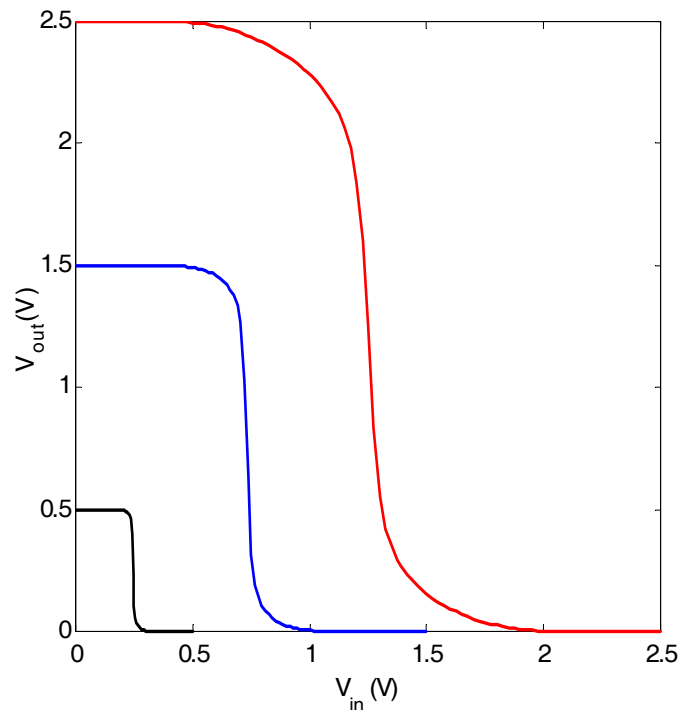
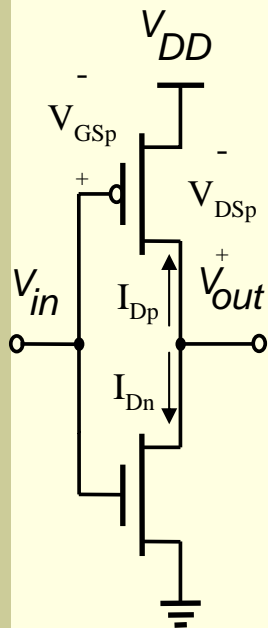
$$V_{IH} - V_{IL} = -\frac{(V_{OH} - V_{OL})}{g} = \frac{-V_{DD}}{g}$$

$$V_{IH} = V_M - \frac{V_M}{g} \quad V_{IL} = V_M + \frac{V_{DD} - V_M}{g}$$

$$NM_H = V_{DD} - V_{IH} \quad NM_L = V_{IL}$$

For regeneration $-g > 1$, g is the gain in transition region

Static characteristics - 10 Scaling the supply voltage

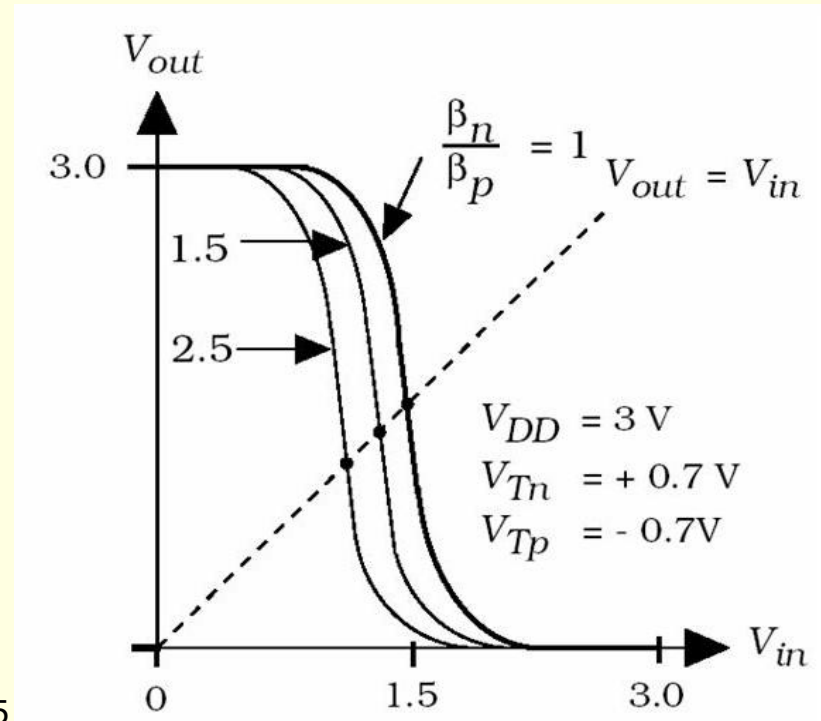
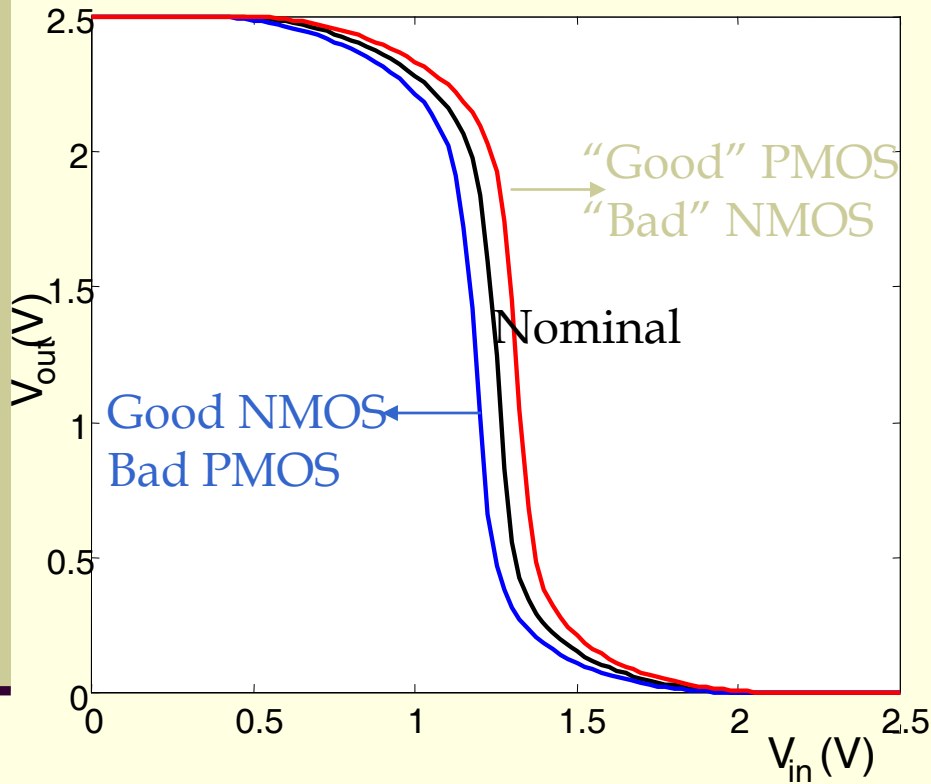


Effects of supply voltage reduction:

- Energy dissipation decreases but gate delay increases
- dc characteristic becomes more sensitive to variations in device parameters
- Signal swing reduces making the design more sensitive to external noise sources that do not scale

Source: Rabaey

Static characteristics -11 Impact of Process Variations



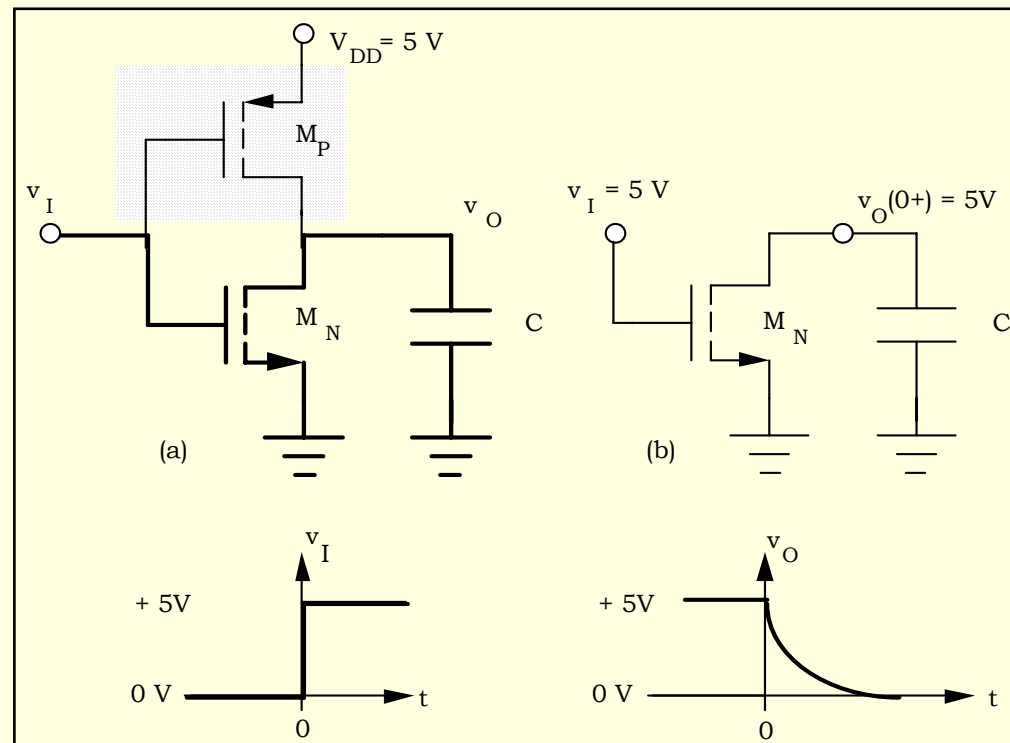
Notes:

1. $k'_n \approx 2 \text{ to } 3 k'_p$
2. For $\beta_n = \beta_p$ and $V_{Tp} = -V_{Tn}$, $V_M = V_{DD}/2$

$$\beta = k' \frac{W}{L}$$

Dynamic operation - 1

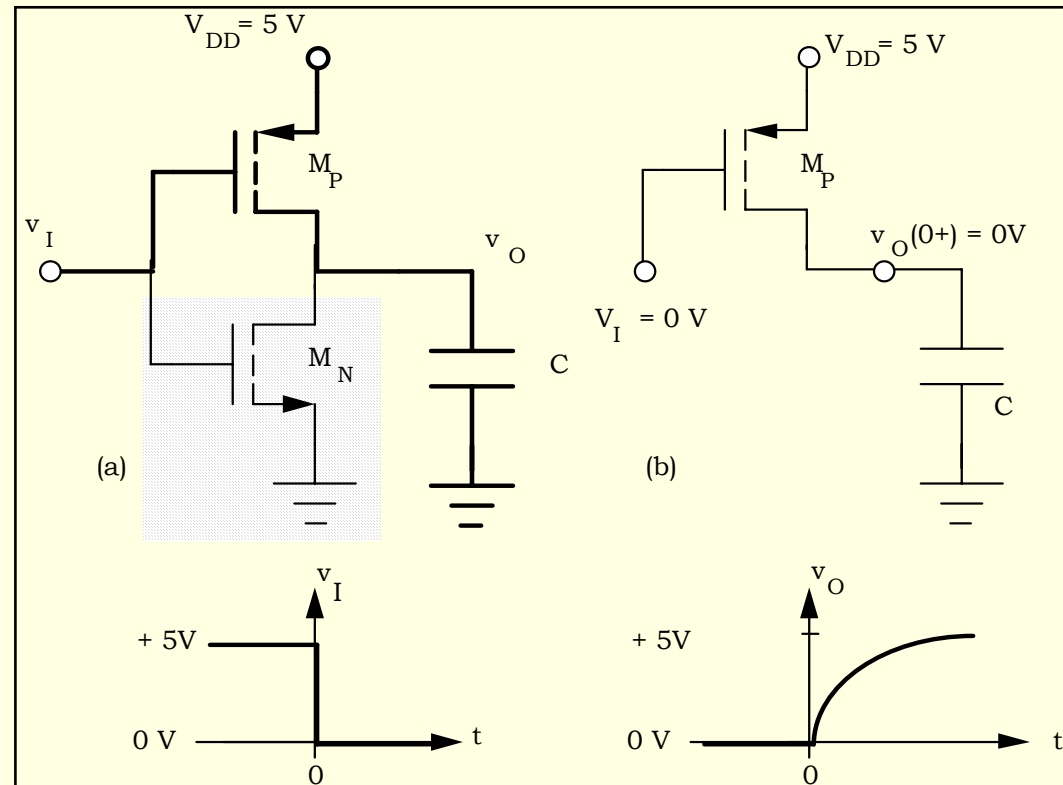
High-to-low output transition in a CMOS inverter



C: load capacitance + interconnect capacitance + capacitances associated with the inverter transistors

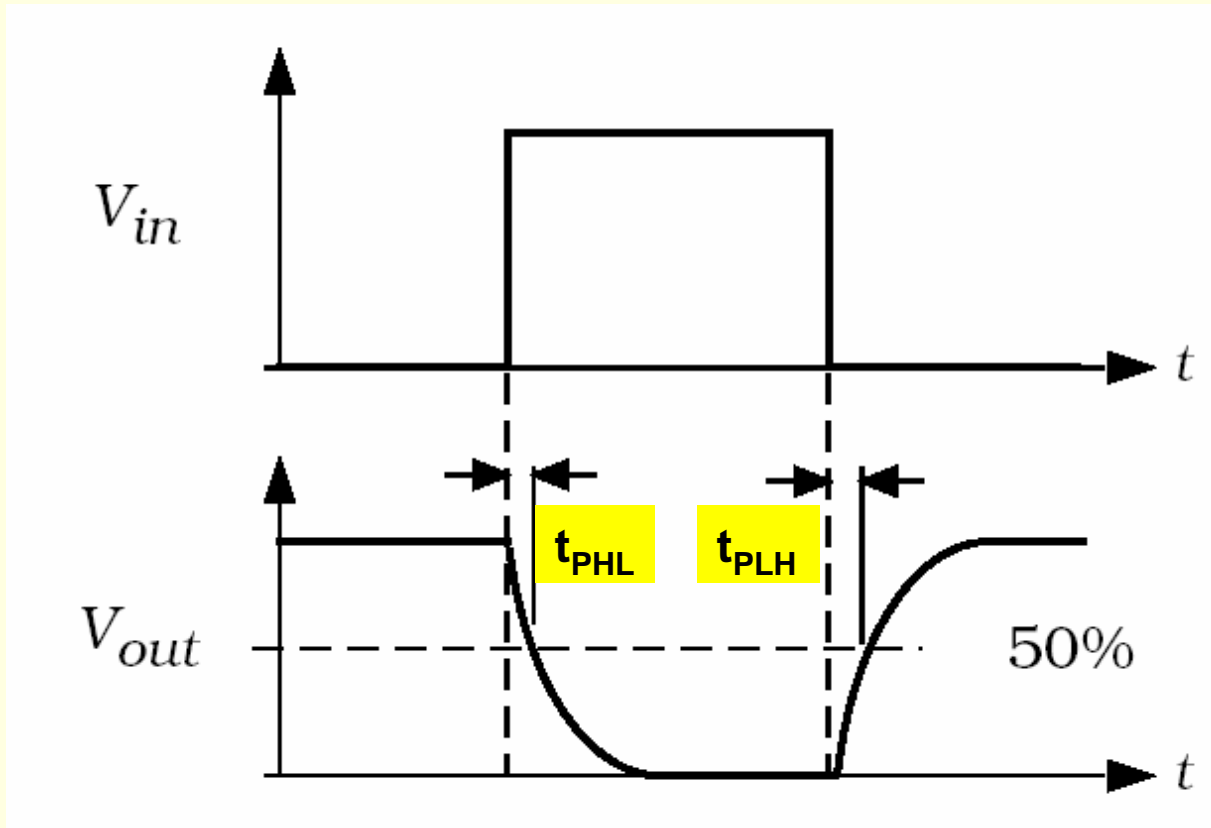
Dynamic operation - 2

Low-to-high output transition in a CMOS inverter



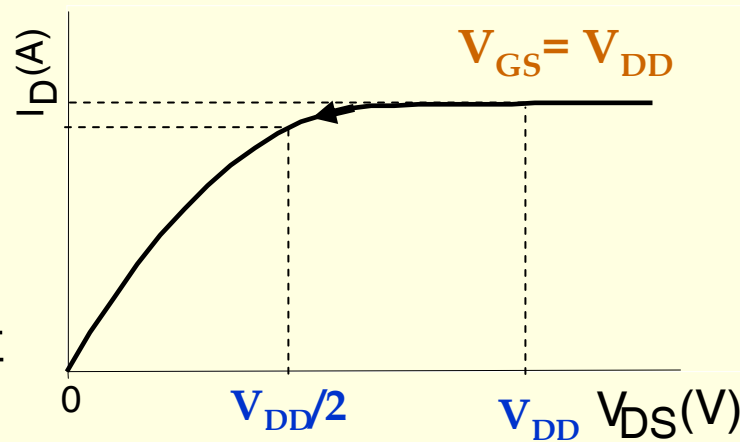
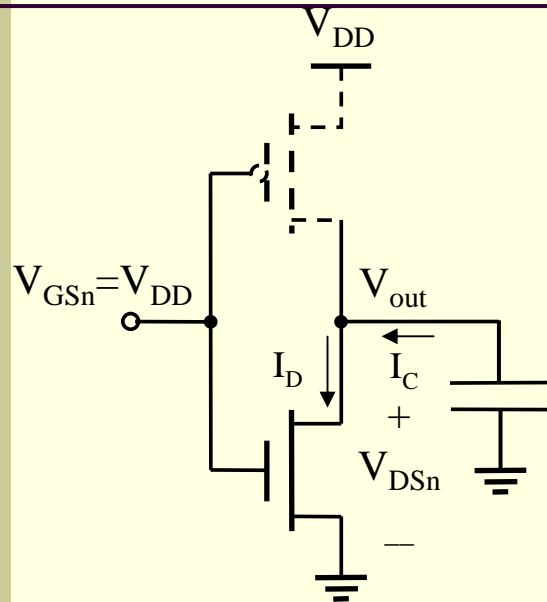
C: load capacitance + interconnect capacitance + capacitances associated with the inverter transistors

Dynamic operation - 3



Dynamic operation - 4

Propagation delay - 1



$$I_D = I_C = -C \frac{dV_{out}}{dt}$$

$$t = 0 \rightarrow V_{out} = V_{DD}$$

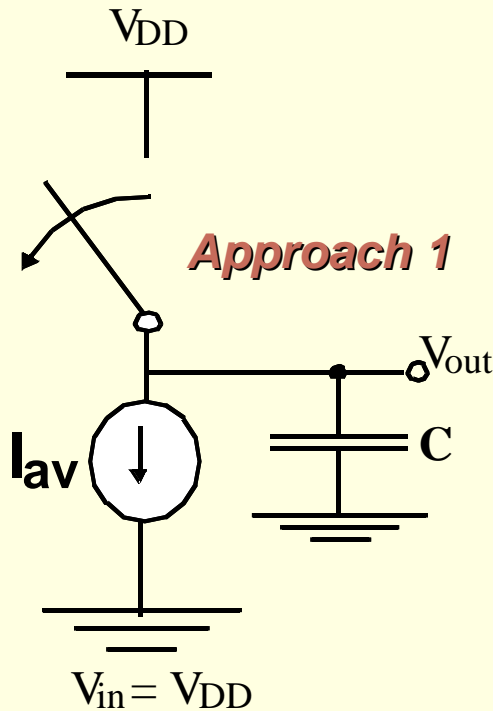
$$t = t_{PHL} \rightarrow V_{out} = V_{DD} / 2$$

$$\int_0^{t_{PHL}} dt = - \int_{V_{DD}}^{V_{DD}/2} C \frac{dV_{out}}{I_D} \rightarrow t_{PHL} = \frac{CV_{DD}/2}{I_{Dav}}$$

$$I_{Dav} = \frac{1}{V_{DD}/2} \int_{V_{DD}/2}^{V_{DD}} I_D(V_{DS}) dV_{DS}$$

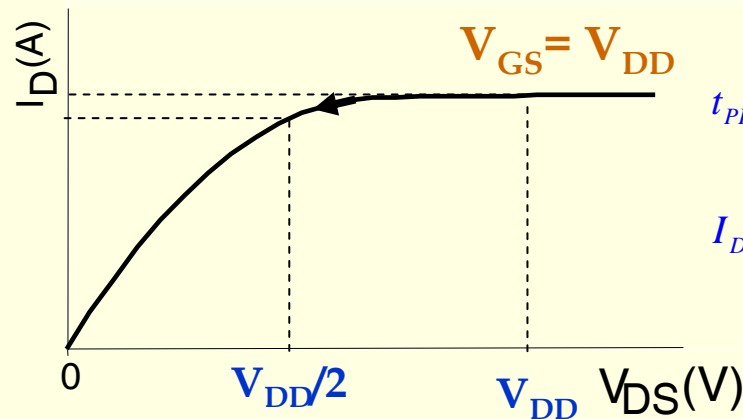
Dynamic operation - 5

Propagation delay - 2



Let us assume that

In this case we have



$$t_{PHL} = \frac{CV_{DD}/2}{I_{D_{av}}}$$

$$I_{D_{av}} = \frac{1}{V_{DD}/2} \int_{V_{DD}/2}^{V_{DD}} I_D(V_{DS}) dV_{DS}$$

$$I_D \cong \frac{k_n}{2} \left(\frac{W}{L} \right)_n (V_{GS} - V_{Tn})^2 \text{ for } V_{DS} > V_{GS} - V_{Tn}$$

$$I_D \cong k_n \left(\frac{W}{L} \right)_n \left[(V_{GS} - V_{Tn})V_{DS} - \frac{V_{DS}^2}{2} \right] \text{ for } V_{DS} \leq V_{GS} - V_{Tn}$$

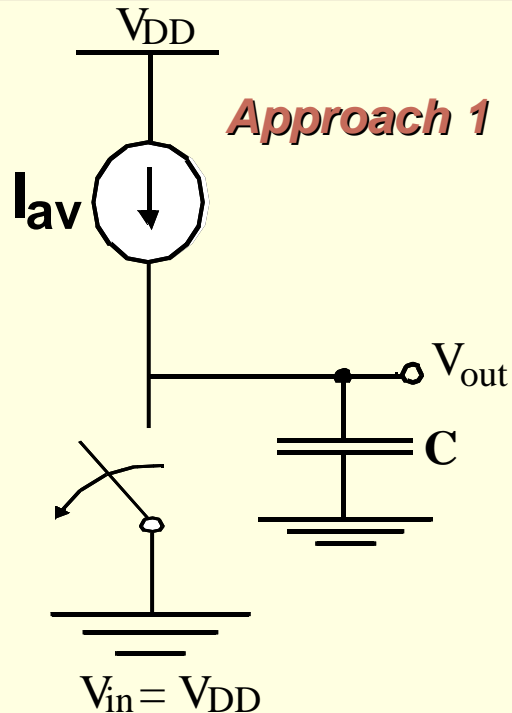
$$I_{D_{av}} \cong I_{D_{sat}} = \frac{k_n}{2} \left(\frac{W}{L} \right)_n (V_{DD} - V_{Tn})^2 \text{ and that } V_{DD} \gg V_{Tn}$$

$$t_{PHL} = \frac{CV_{DD}/2}{I_{D_{av}}} \approx \frac{CV_{DD}/2}{\frac{k_n}{2} \left(\frac{W}{L} \right)_n (V_{DD} - V_{Tn})^2};$$

$$t_{PHL} \approx \frac{C}{k_n \left(\frac{W}{L} \right)_n V_{DD}}$$

Dynamic operation - 6

Propagation delay - 3



$$I_{Dav} \cong I_{Dsat} = \frac{k_p}{2} \left(\frac{W}{L}\right)_p (V_{DD} + V_{Tp})^2 \text{ and that } V_{DD} \gg -V_{Tp}$$

$$t_{PLH} = \frac{CV_{DD}/2}{I_{Dav}} \approx \frac{CV_{DD}/2}{\frac{k_p}{2} \left(\frac{W}{L}\right)_p (V_{DD} + V_{Tp})^2};$$

$$t_{PLH} \approx \frac{C}{k_p \left(\frac{W}{L}\right)_p V_{DD}}$$

$$t_p = \frac{t_{PLH} + t_{PHL}}{2}$$

$$t_{PHL} \approx \frac{C}{k_n \left(\frac{W}{L}\right)_n V_{DD}}$$

Comments:

- $k_n \approx 2-3 k_p$, $k_{n,p} = \mu_{n,p} \cdot C_{ox}$
- Increasing V_{DD} reduces t_p but power goes up
- t_{PLH} can be $\approx t_{PHL}$ by making $(W/L)_p \approx 2-3(W/L)_n$ BUT C is dependent on transistor dimensions
- C includes load (fan-out), wire, inverter "self-capacitance"
- C is non linear

Dynamic operation - 7

Propagation delay - 4

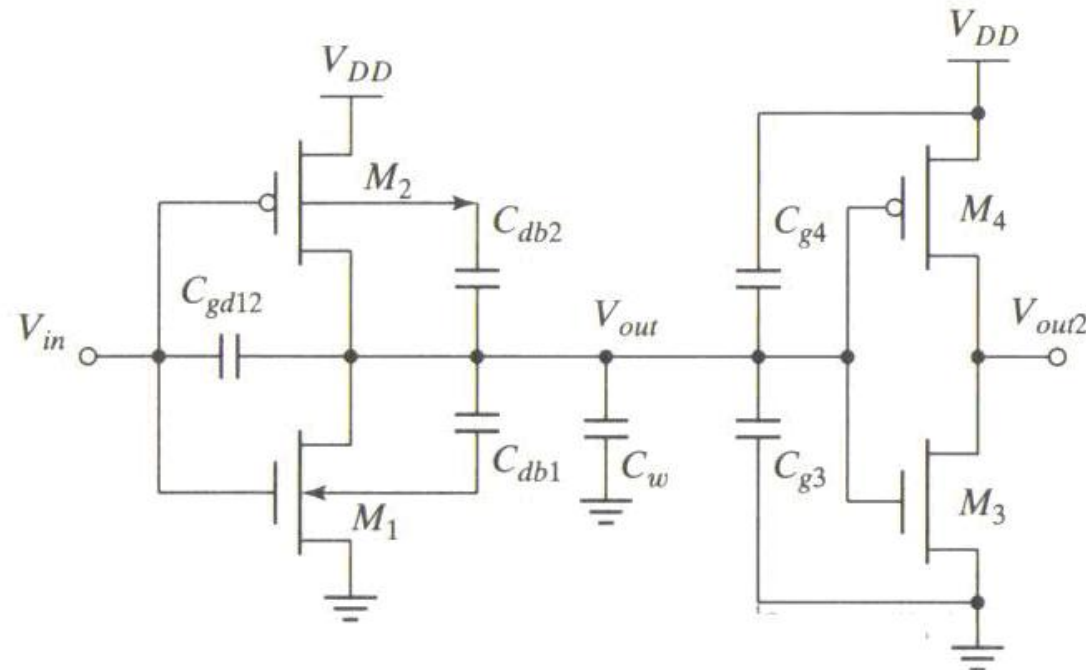
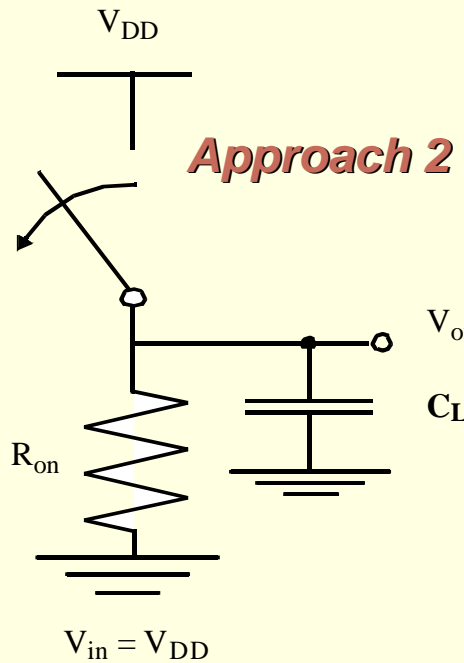


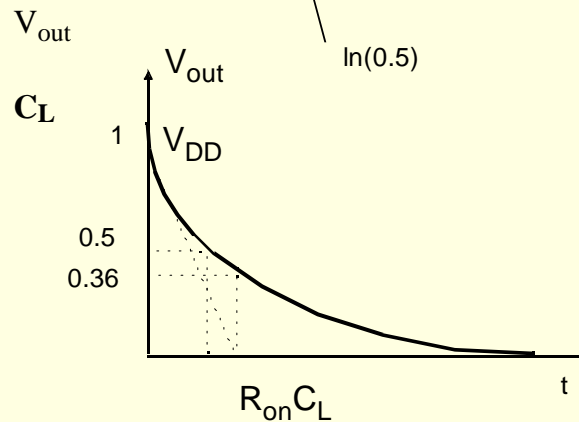
Figure 5-13 Parasitic capacitances, influencing the transient behavior of the cascaded inverter pair.

Dynamic operation - 8

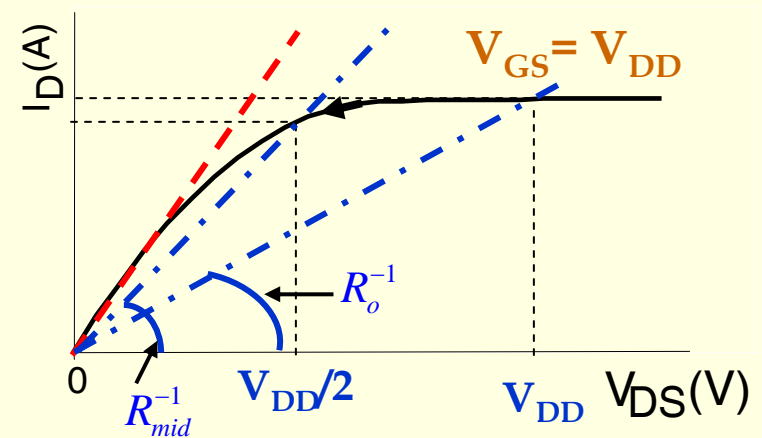
Propagation delay - 5



$$t_{pHL} = f(R_{on} \cdot C_L) = 0.69 R_{on} C_L$$



What's R_{on} ?



Approach by Uyemura

$$R_{on}^{-1} = \left. \frac{dI_D}{dV_{DS}} \right|_{V_{DS}=0} = k_n \left(\frac{W}{L} \right)_n (V_{DD} - V_{Tn})$$

Approach by Rabaey

$$R_{on} \equiv \frac{1}{2} (R_0 + R_{mid})$$

Modeling capacitor discharge as in an RC circuit!

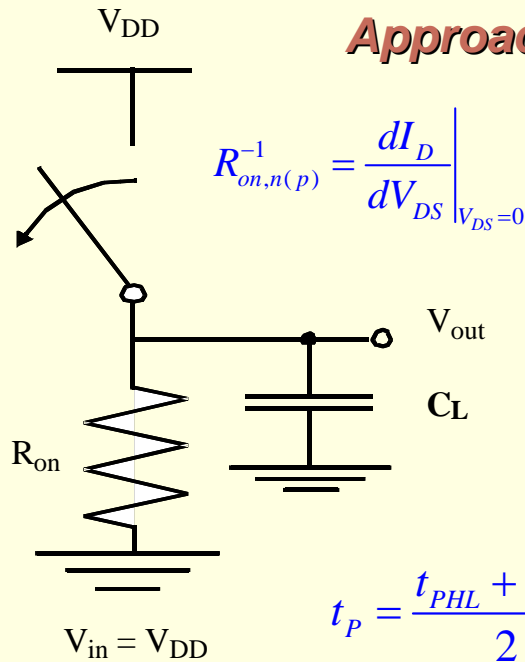
$$t_{PHL} \approx \frac{C}{k_n \left(\frac{W}{L} \right)_n V_{DD}}$$

Source: Rabaey

Dynamic operation - 9

Propagation delay - 6

Approach by Uyemura



$$R_{on,n(p)}^{-1} = \left. \frac{dI_D}{dV_{DS}} \right|_{V_{DS}=0} = k_{n(p)} \left(\frac{W}{L} \right)_{n(p)} (V_{DD} - (+)V_{Tn(p)})$$

$$t_{pHL} = 0.69 R_{on,n} C_L$$

$$t_{pLH} = 0.69 R_{on,p} C_L$$

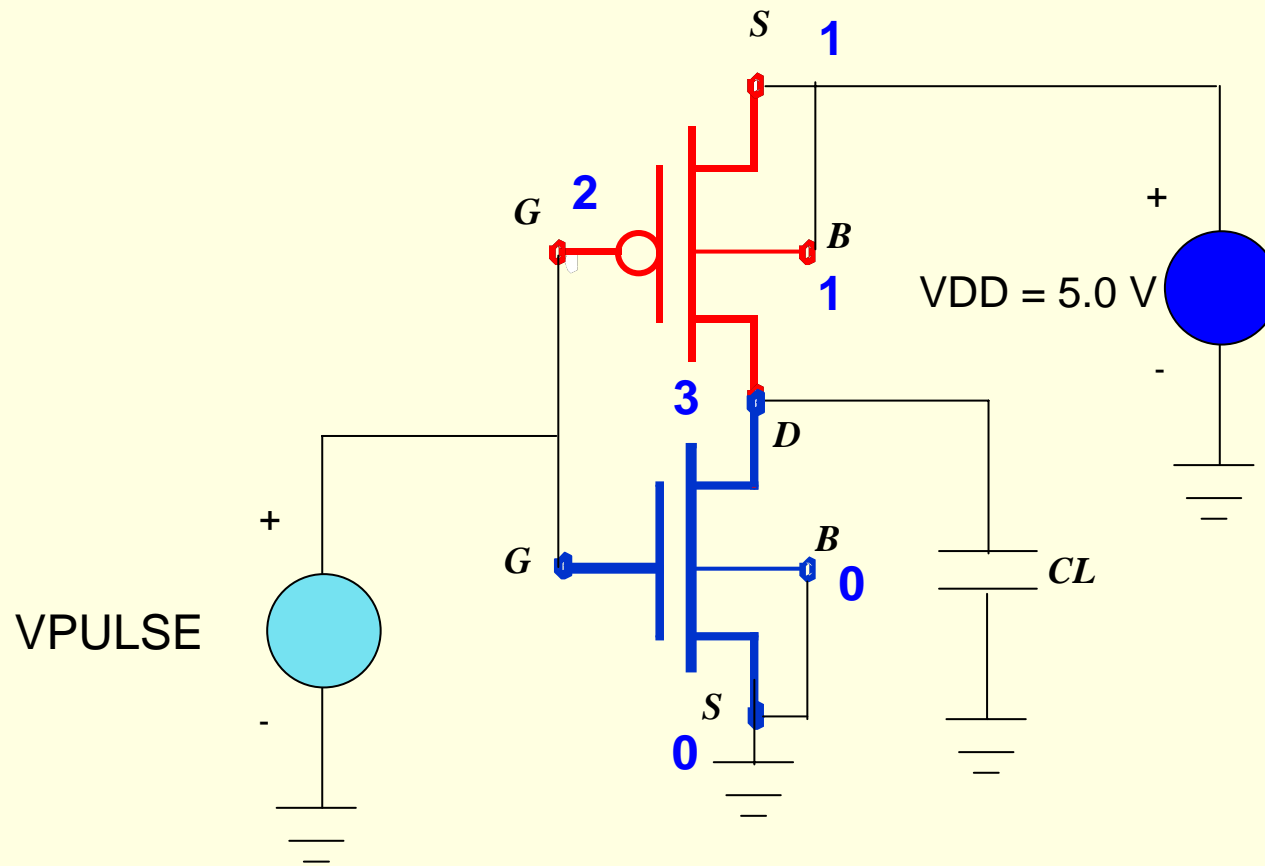
$$t_p = \frac{t_{PHL} + t_{PLH}}{2} = \frac{0.69 \cdot C_L}{2} \left[\frac{1}{k_n \left(\frac{W}{L} \right)_n (V_{DD} - V_{Tn})} + \frac{1}{k_p \left(\frac{W}{L} \right)_p (V_{DD} + V_{Tp})} \right]$$

$$t_p \approx \frac{0.69 \cdot C_L}{2V_{DD}} \left[\frac{1}{k_n \left(\frac{W}{L} \right)_n} + \frac{1}{k_p \left(\frac{W}{L} \right)_p} \right]$$

Source: Uyemura

Dynamic operation - 10

Experimental setup



Dynamic operation - 11

Inverter Propagation Delay

* this is the Propagationdelay.cir file

* PMOS transistor description

MP 3 2 1 1 modelp W=2u L=1u

.model modelp pmos (level=1 VT0=-0.65 TOX=7.5n KP=60u lambda=0.0)

* NMOS transistor description

MN 3 2 0 0 modeln W=2u L=1u

.model modeln nmos (level=1 VT0=0.5 TOX=7.5n KP=150u lambda=0.0)

* dc source

vDD 1 0 dc 5.0

*load capacitance

CL 3 0 0.01p

*signal source

v0 2 0 dc 0 pulse 0 5 0 1ps 1ps 200ps 400ps

.end

Dynamic operation - 12

SpiceOpus (c) 6 -> source Propagationdelay1.cir

SpiceOpus (c) 7 -> tran 1ps 500ps

SpiceOpus (c) 8 -> setplot

new New plot

Current tran2 Inverter Propagation Delay (Transient Analysis)

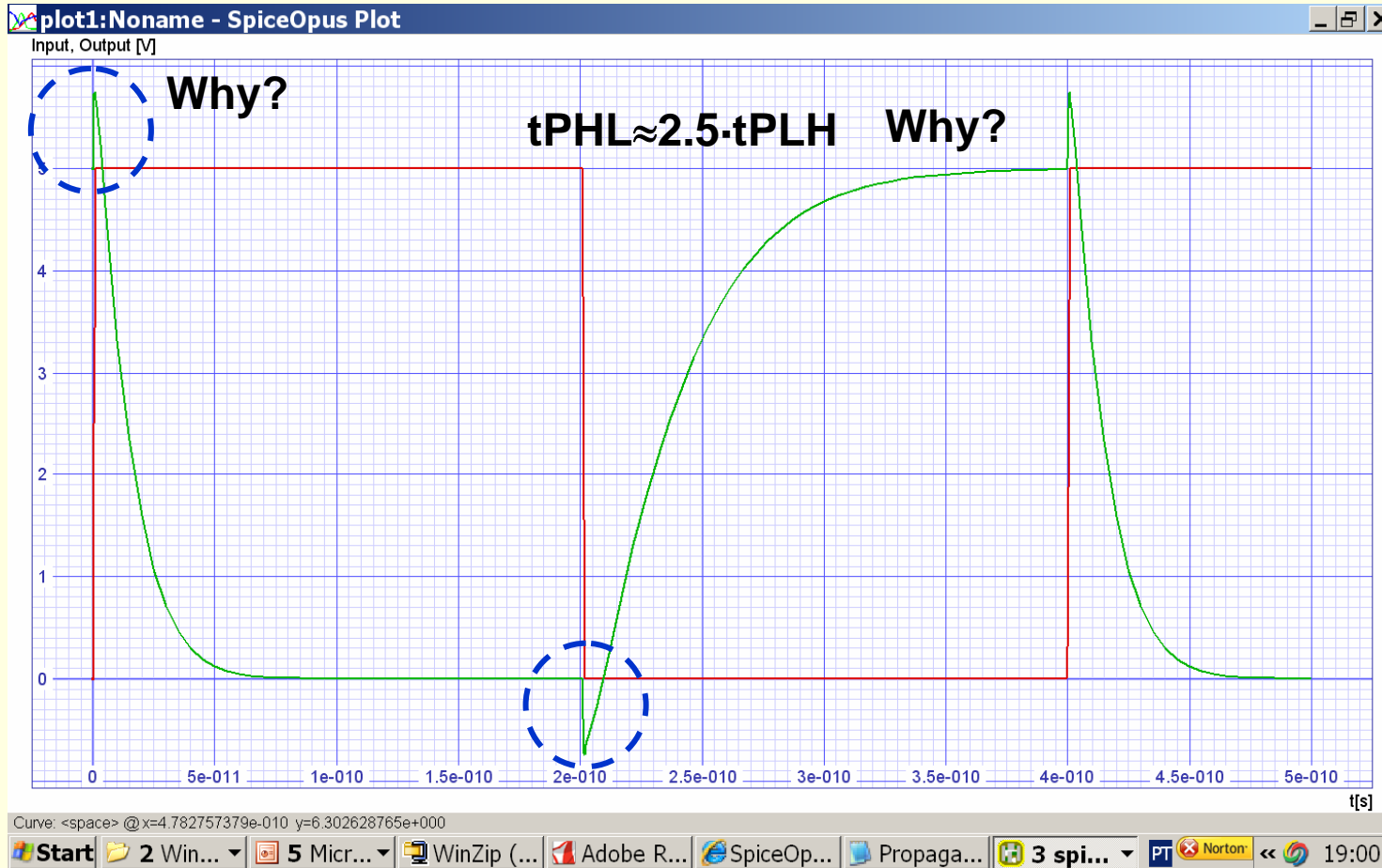
tran1 Inverter Propagation Delay (Transient Analysis)

const Constant values (constants)

SpiceOpus (c) 9 -> setplot tran2

SpiceOpus (c) 10 -> plot v(2) v(3) xlabel t[s] ylabel 'Input, Output [V]'

Dynamic operation - 12



Dynamic operation - 14

Exercise

Simulate the transient response of the inverter of the previous exercise for fan-outs of one and two inverters

Dynamic operation - 15

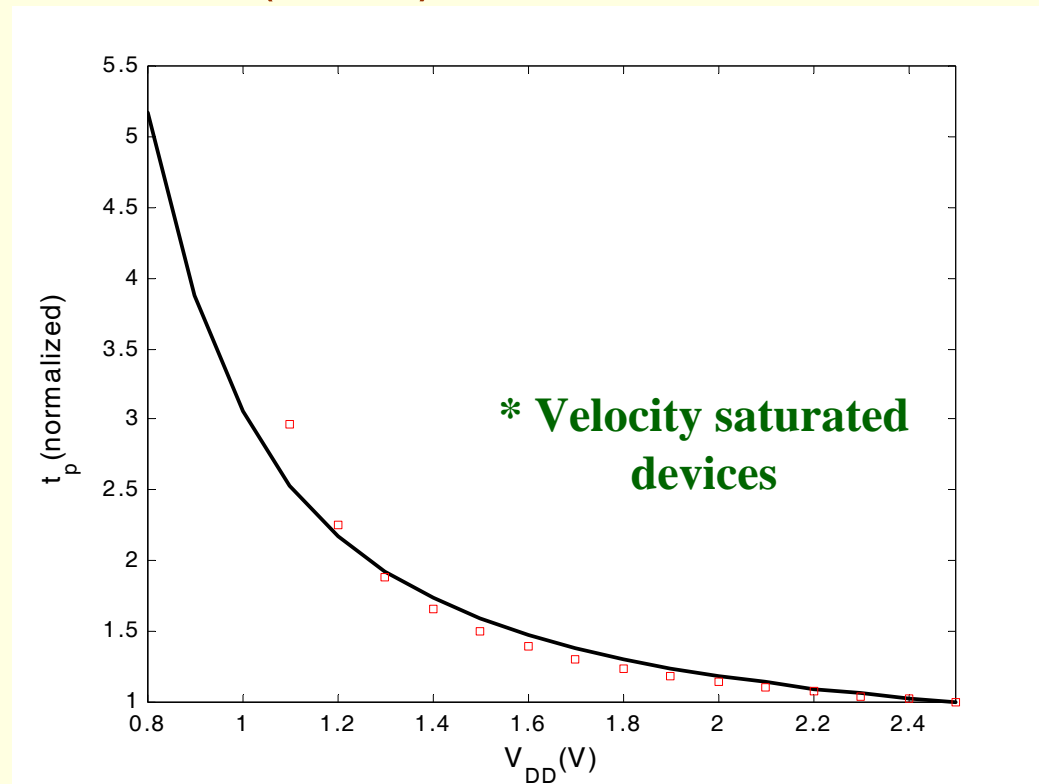
Design for Performance

- Keep capacitances small
- Increase transistor sizes (W)
 - watch out for self-loading!
- Increase V_{DD} (????)

Dynamic operation - 16

Design for Performance

- Increase V_{DD} (????)

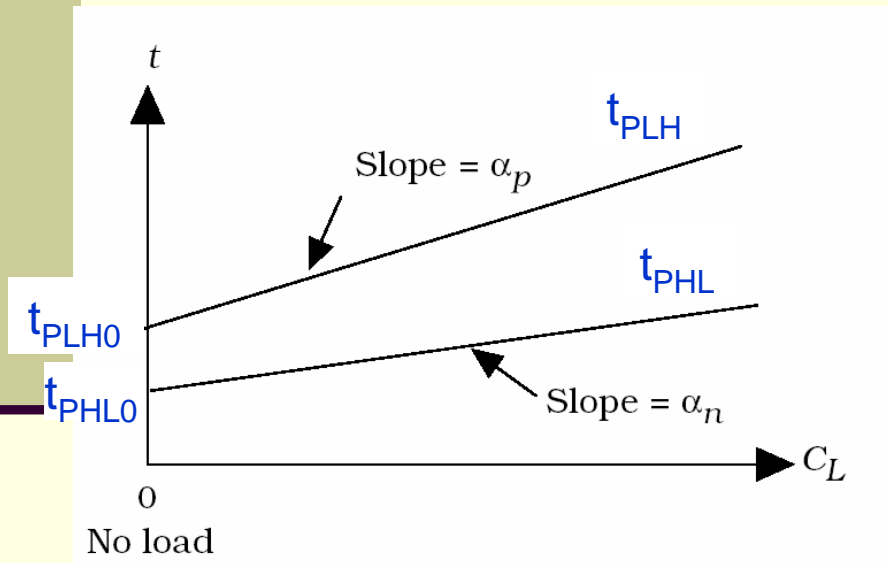
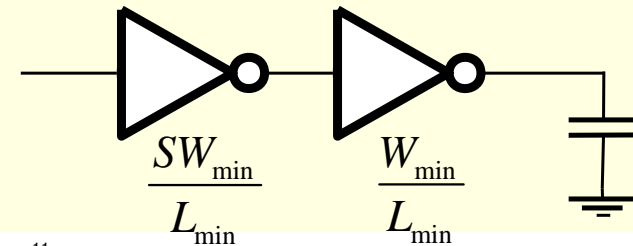


Source: Rabaey

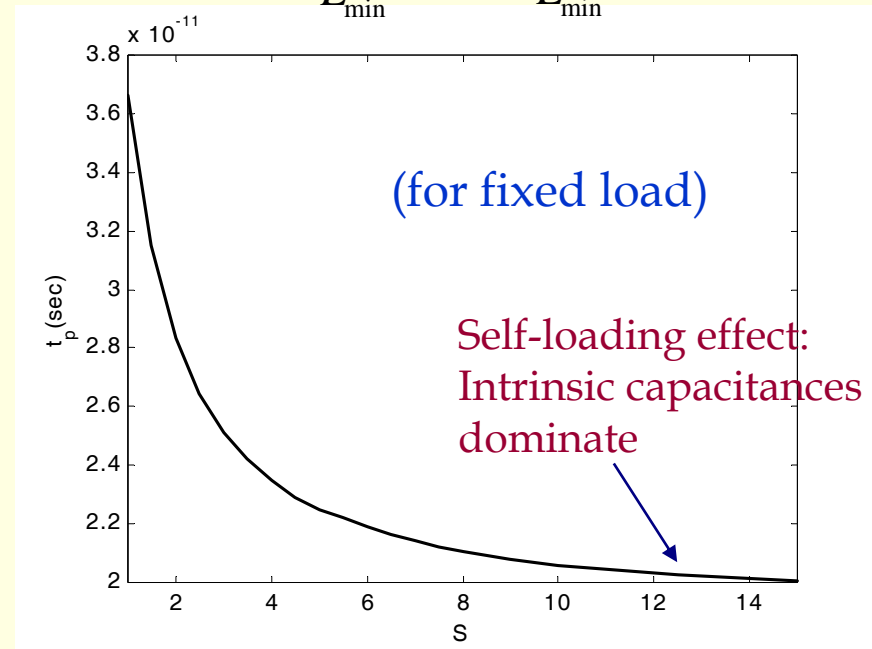
Dynamic operation - 17

Design for Performance

- Increase transistor sizes (W)
 - watch out for self-loading

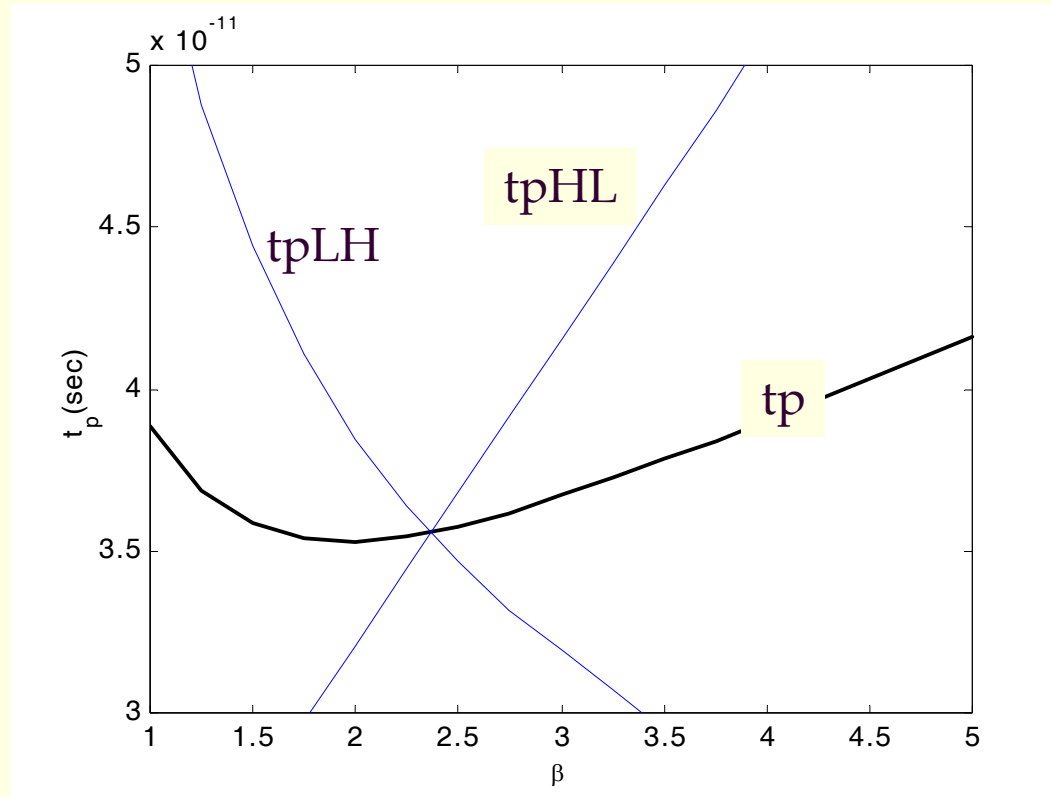


Propagation delays vs. load capacitance



Dynamic operation - 18

Design for Performance

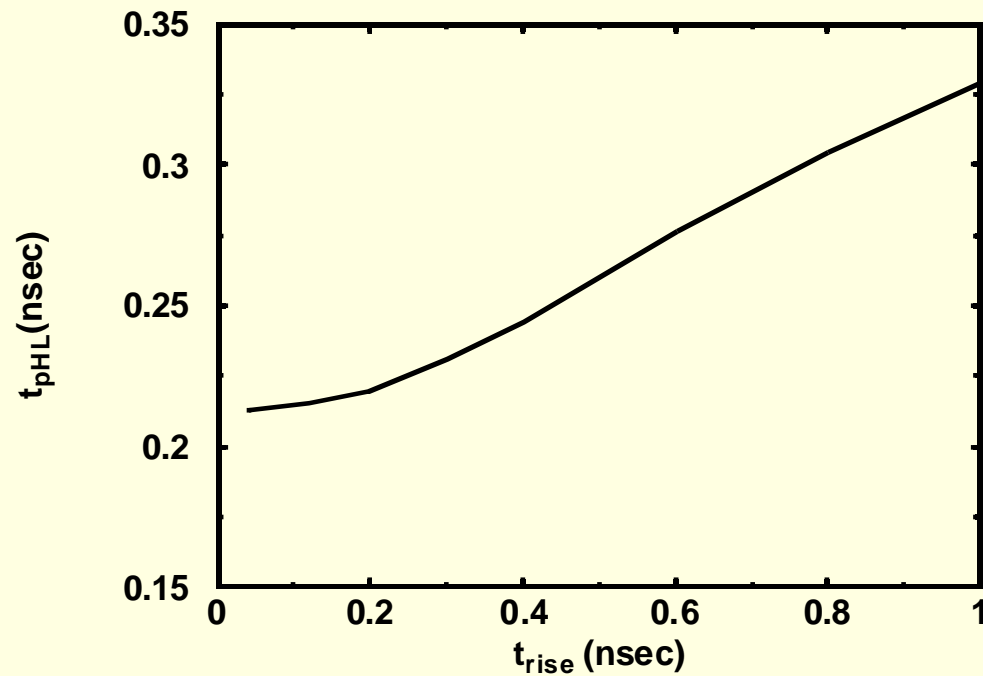


Propagation delays vs. PMOS-to-NMOS transistor ratio $\beta = W_p/W_n$

Source: Rabaey

Dynamic operation - 19

Impact of Rise Time on Delay



$$t_{pHL} = \sqrt{t_{pHL(step)}^2 + (t_r/2)^2}$$

Source: Rabaey